

# Degradation Mechanisms in TOPCon/POLO Solar Cells

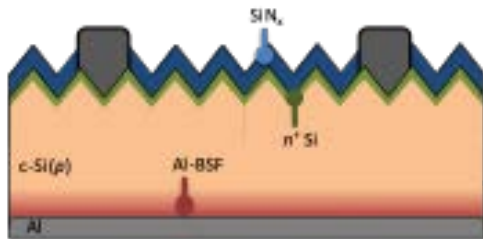
David Young  
NREL

# What is a TOPcon cell?

Old Technology

- P-diffused emitter
- Al-“Back surface field”

Al-BSF



Efficiency: 16-20%

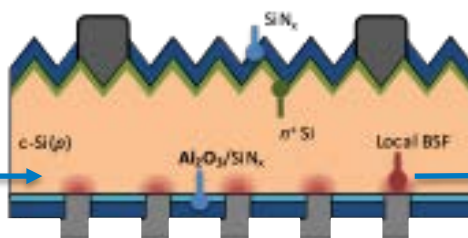
Wafer: P-type wafer

Bulk degradation: LID

Current Standard

- SiNx/Al<sub>2</sub>O<sub>3</sub> passivation
- Laser openings
- Point Al-BSF contacts

PERC



~22-24.5%

P-type wafer

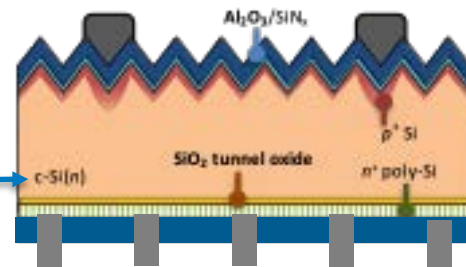
LID, LeTID

Next Generation

(likely US buildout)

- B-diffused junction
- SiO<sub>2</sub>/Poly-Si back contact

TOPCon



~24-26%

(28.7% Theo. max  $\eta$ )

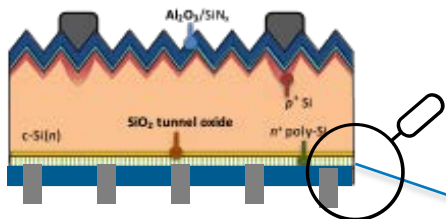
N-type wafer

LeTID

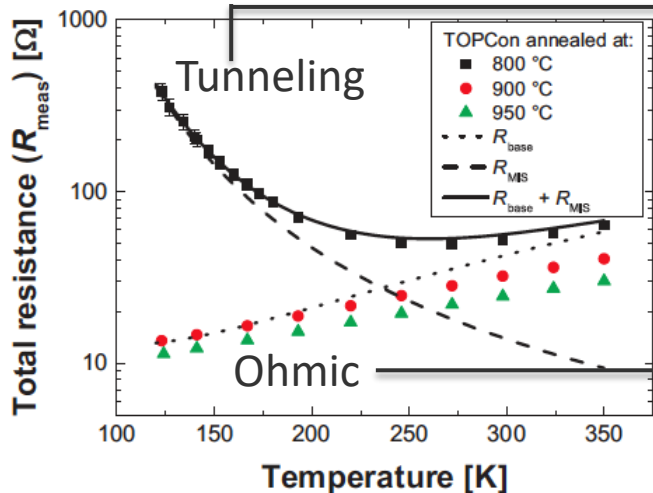
SiO<sub>2</sub>  
n-polySi:P  
SiN<sub>x</sub> (Al<sub>2</sub>O<sub>3</sub>)

# SiO<sub>2</sub>/Poly-Si Contacts

TOPCon cell

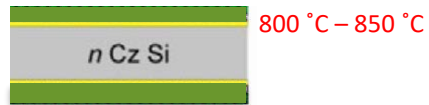


Different transport mechanisms

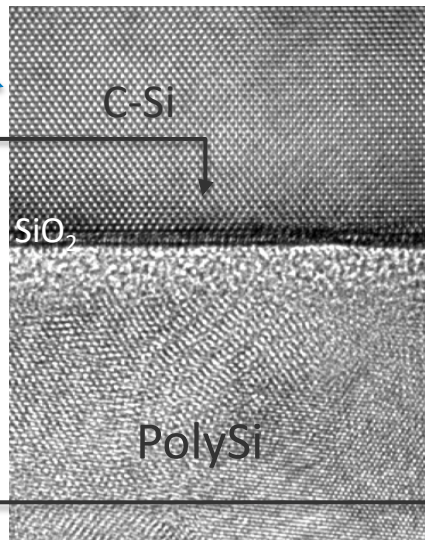


“TOPCon contact”

Tunnel Oxide Passivated Contact

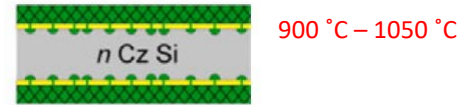


Uniform tunneling oxide ~1.5 nm

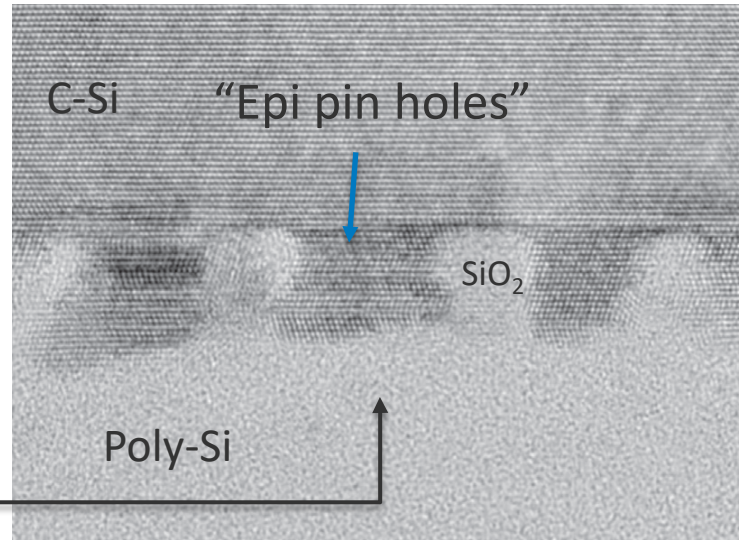


“POLO contact”

POLycrystalline silicon on Oxide

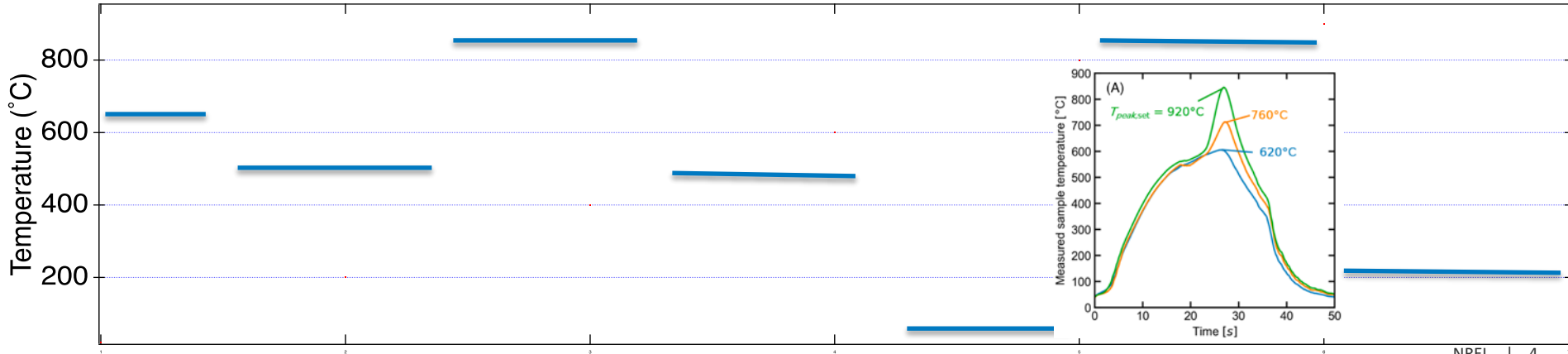
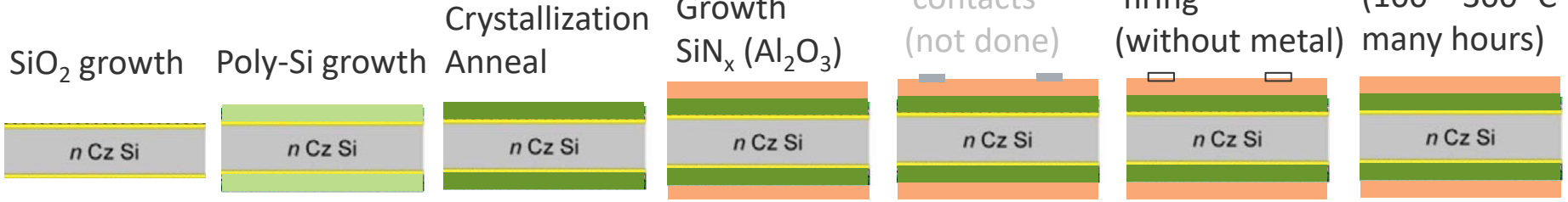
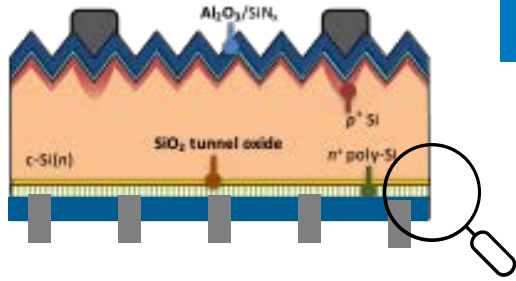


2.4 nm oxide -> Pin holes



“PolySilicon Emitters for silicon concentrator solar cells”  
 Jon-Yiew Gan, Stanford University 1990 *thesis*. Dr. Swanson advisor

# Symmetric Poly-Si/SiO<sub>2</sub> contact samples



# $\tau_{\text{effective}}$ and $J_0$

(B-O LID, LeTID)

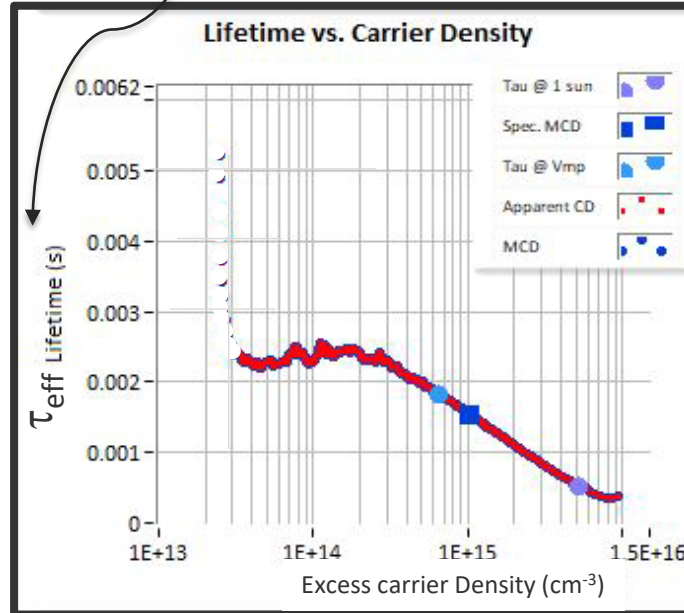
Surface recombination parameter ( $\text{fA}/\text{cm}^2$ )

Measured by  
Photoconductance Decay tool  
(Sinton lifetime tester)



$$\frac{1}{\tau_{\text{eff}}} = \frac{1}{\tau_{\text{SRH}}} + \frac{1}{\tau_{\text{A-M}}} + \frac{1}{\tau_{\text{rad}}} + \frac{2J_0(N_{\text{dop}} + \Delta n)}{qWn_i^2}$$

Annotations in the image:  
 - An arrow points from the text "(B-O LID, LeTID)" to the  $\frac{1}{\tau_{\text{SRH}}}$  term.  
 - An arrow points from the text "(1-10 ms)" to the  $\tau_{\text{eff}}$  term.  
 - An arrow points from the text "< 10 fA/cm<sup>2</sup>" to the  $2J_0(N_{\text{dop}} + \Delta n)$  term.





# $\tau_{\text{effective}}$ and $J_0$

(B-O LID, LeTID)

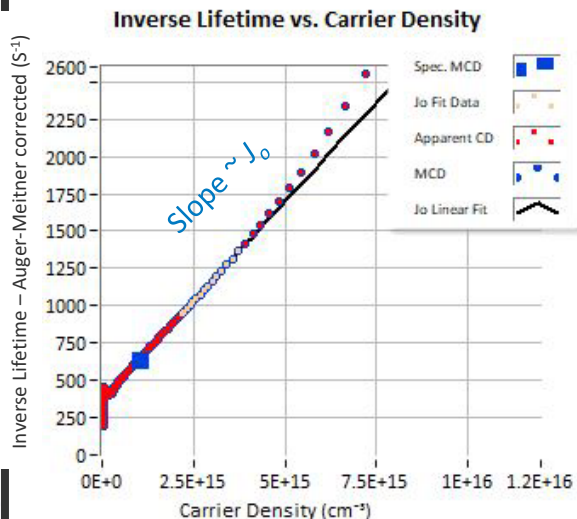
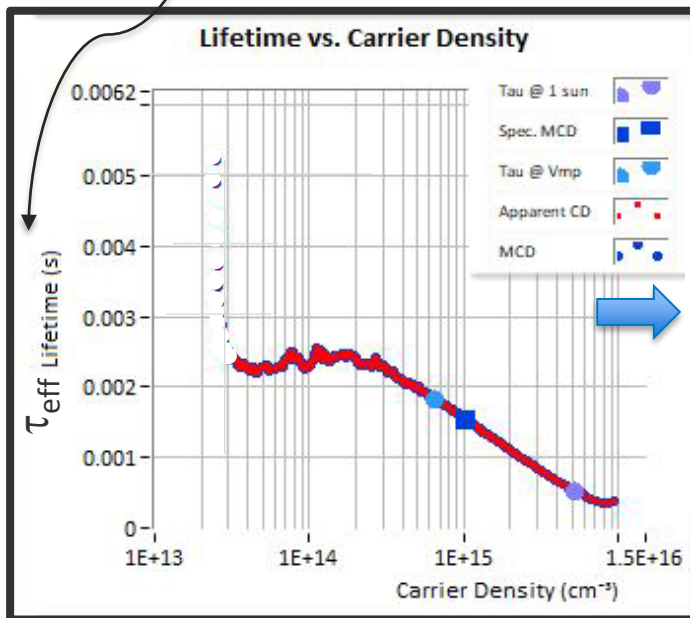
Surface recombination parameter ( $\text{fA}/\text{cm}^2$ )

Measured by  
Photoconductance Decay tool  
(Sinton lifetime tester)



$$\frac{1}{\tau_{\text{eff}}} = \frac{1}{\tau_{\text{SRH}}} + \frac{1}{\tau_{\text{A-M}}} + \frac{1}{\tau_{\text{rad}}} + \frac{2J_0(N_{\text{dop}} + \Delta n)}{qWn_i^2}$$

(1-10 ms)      (< 10 fA/cm<sup>2</sup>)



# $\tau_{\text{effective}}$ and $J_0$



Measured by  
Photoconductance Decay tool  
(Sinton lifetime tester)

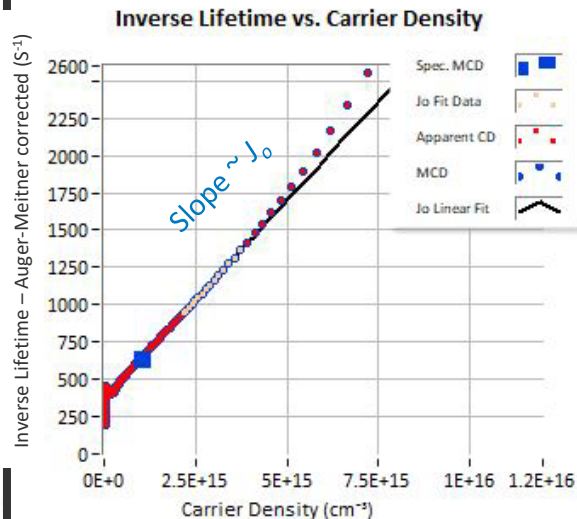
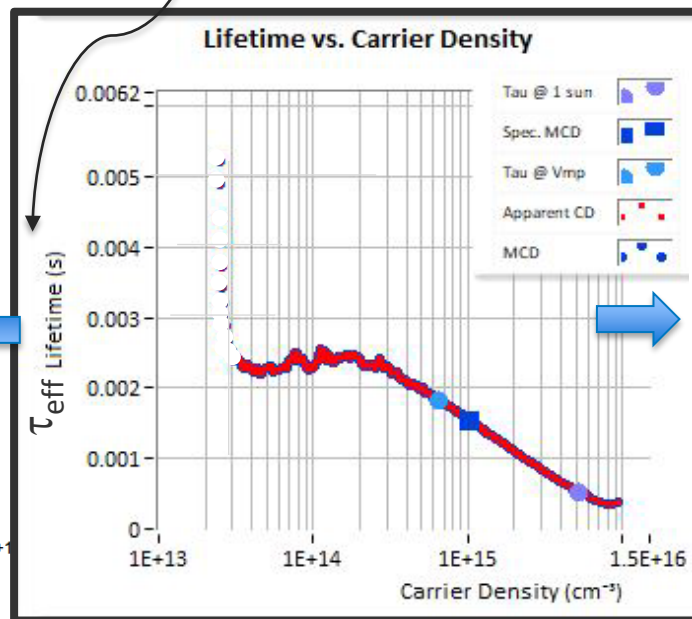
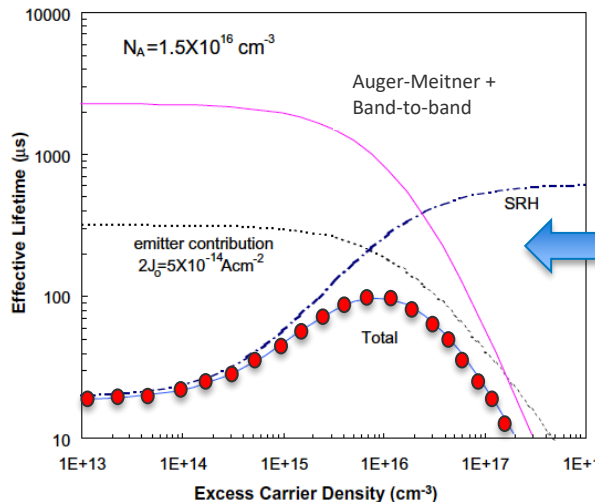
(B-O LID, LeTID)

Surface recombination parameter ( $\text{fA}/\text{cm}^2$ )

$$\frac{1}{\tau_{\text{eff}}} = \frac{1}{\tau_{\text{SRH}}} + \frac{1}{\tau_{\text{A-M}}} + \frac{1}{\tau_{\text{rad}}} + \frac{2J_0(N_{\text{dop}} + \Delta n)}{qWn_i^2}$$

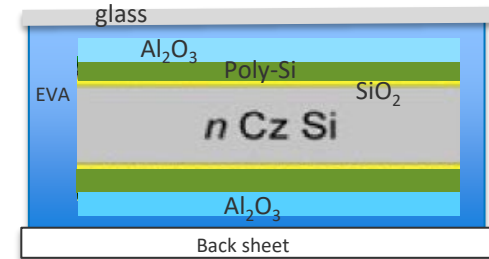
(1-10 ms)

( $< 10 \text{ fA}/\text{cm}^2$ )



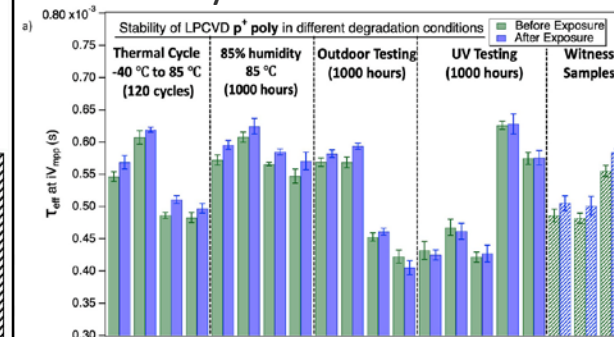
# Non-Fired Encapsulated PolySi/SiO<sub>2</sub> Contacts

- Symmetric n-type TOPCon contact structures
- Glass/back sheet mini module

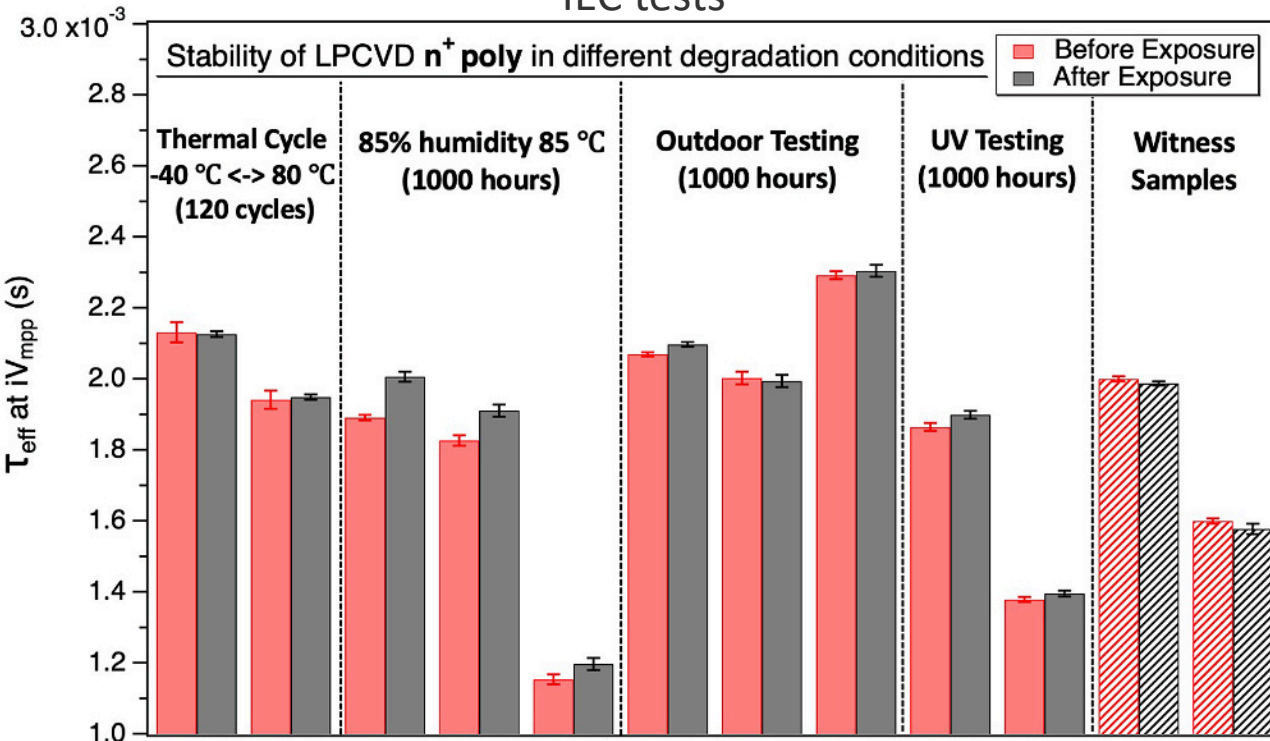


- No degradation under IEC test conditions
- No adhesion issues observed

Same story for p-type  
Poly-Si:B contacts



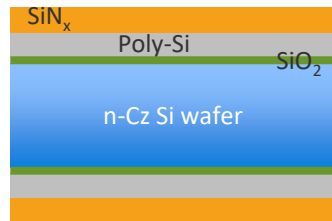
## IEC tests



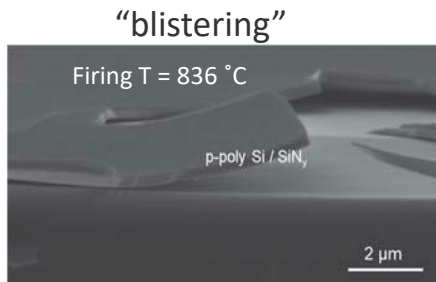
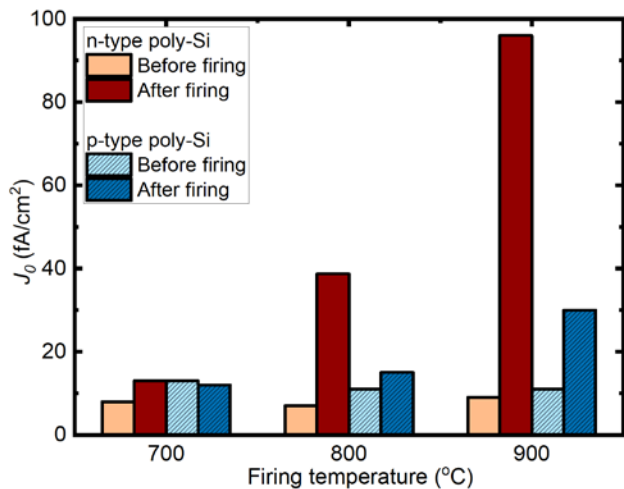
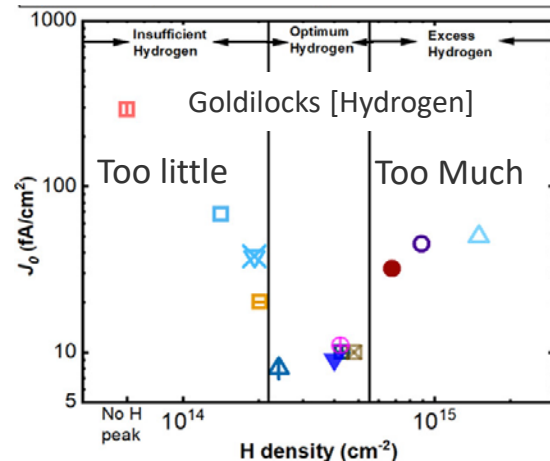


# Fired Symmetric PolySi/SiO<sub>2</sub> Contacts

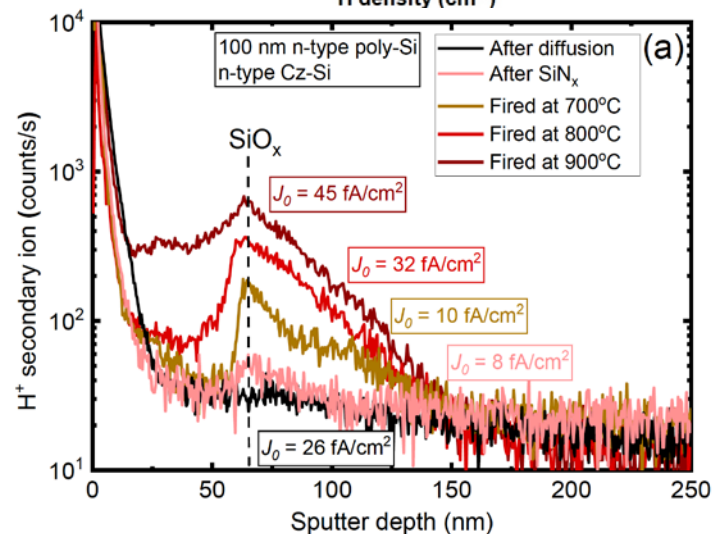
$$T_{\text{fire}} = 800 \text{ } ^\circ\text{C}$$



- Firing lowers surface passivation (increases  $J_0$ )
- Optimum [H] -> Optimum  $J_0$
- H effuses to tunneling SiO<sub>2</sub> layer
- Thermal stress creates defects in Poly-Si layer
- Blisters if  $T_{\text{fire}}$  is too high

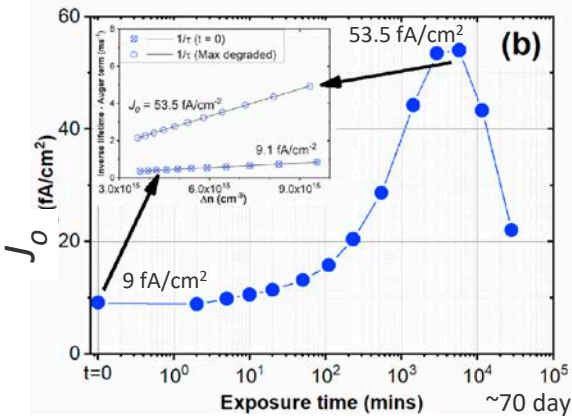
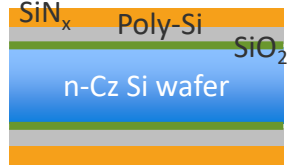
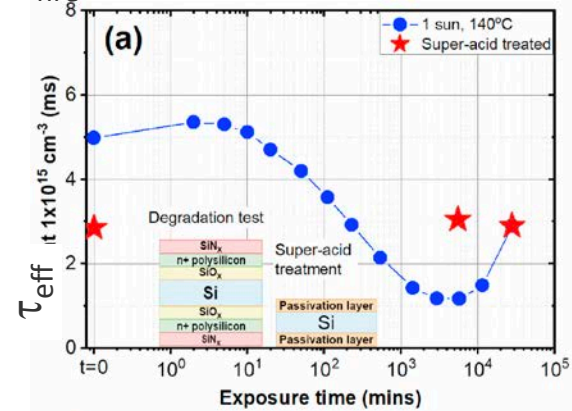


Soeriyadi et al. SiliconPV 2021  
AIP Conf. Proc. 2487, 050006-1



# Poly-Si/SiO<sub>2</sub> Degradation/Regeneration Cycle Observed “Is it LeTID?”

$T_{\text{fire}} = 700\text{ }^{\circ}\text{C} + 140\text{ }^{\circ}\text{C}$ , 1-sun anneal

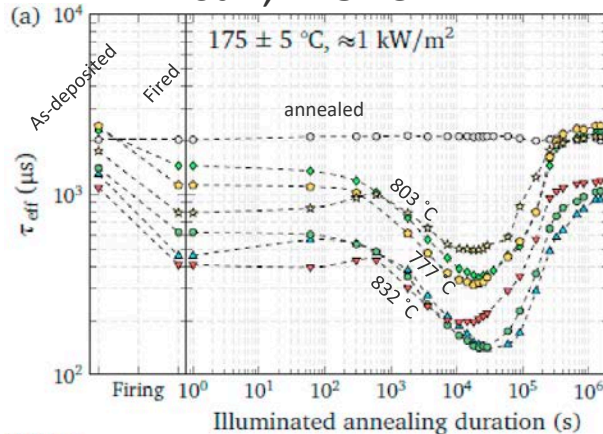


- Degradation followed by regeneration cycle
- $\tau_{\text{eff}}$  decreases due to  $J_0$  increase
  - $J_0$  is constant with LeTID
- $\tau_{\text{bulk}}$  remains constant (super-acid passivation)
  - Bulk changes with LeTID
- Poly-Si did not change structurally (XRD)
- LPCVD and PECVD poly-Si show similar cycle (independent of poly-Si grain size)
- Different SiN<sub>x</sub> layers (density) show slightly different cycles.
  - LeTID cycles vary considerably with SiN<sub>x</sub> parameters

# Poly-Si/SiO<sub>2</sub> Degradation/Regeneration Cycle as a Function of T<sub>fire</sub>

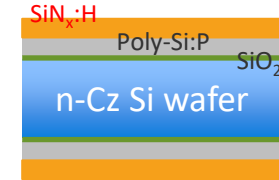
1-sun, 175 °C

T<sub>fire</sub> = 619 - 832 °C

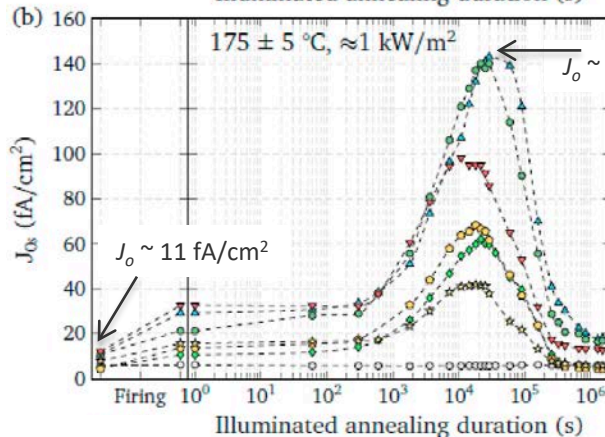


Peak firing T

- Control
- ▲- 619 ± 5 °C
- ◉- 710 ± 3 °C
- ◆- 743 ± 9 °C
- ◇- 777 ± 4 °C
- ☆- 803 ± 7 °C
- ▽- 832 ± 7 °C



- Non-fired, control sample:
  - τ<sub>eff</sub> and J<sub>o</sub> are stable
- Fired samples:
  - τ<sub>eff</sub> and J<sub>o</sub> show degrade/regen cycle improving beyond the as-deposited state
  - No correlation of cycle with firing temperature on
    - time to max degrade/regen
    - magnitude of degrade
    - LeTID shows faster time to degrade and larger magnitude of degradation with increasing T<sub>fire</sub>
  - Hollemann et al. found firing belt speed influences J<sub>o</sub> (temperature gradient)



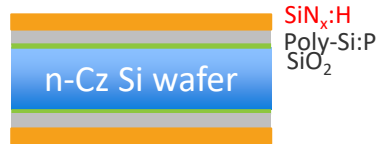
Peak firing T

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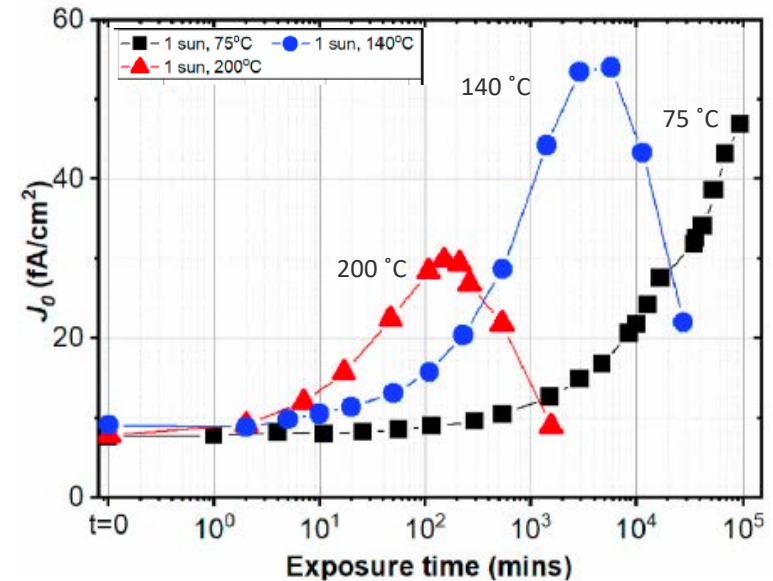
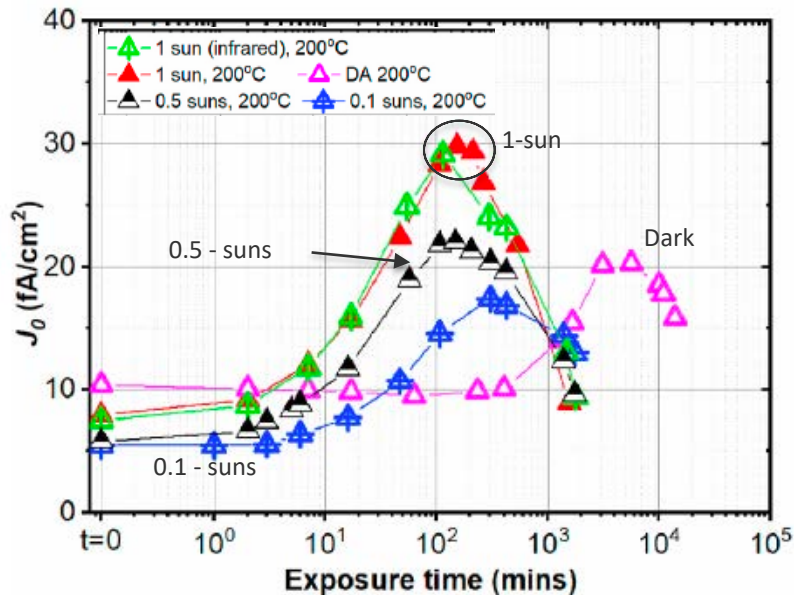
# Annealing Illumination and Temperature

- Degrade/Regen cycle time decreases with increasing illumination.
- Dark anneal shows similar cycle.

$$T_{\text{fire}} = 600 - 770 \text{ } ^\circ\text{C}$$

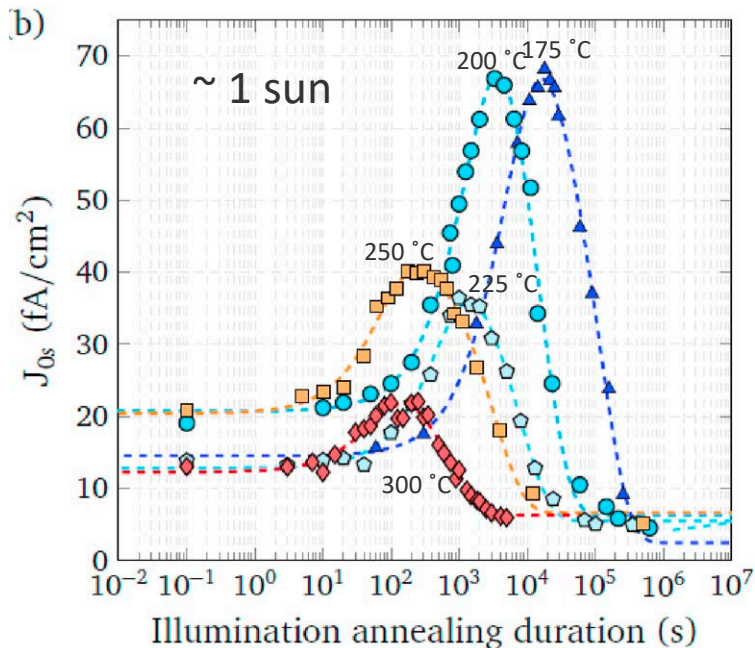


- Degrade/Regen cycle *time* and *magnitude* decrease with increasing annealing temperature.
- Cycle is a thermal process

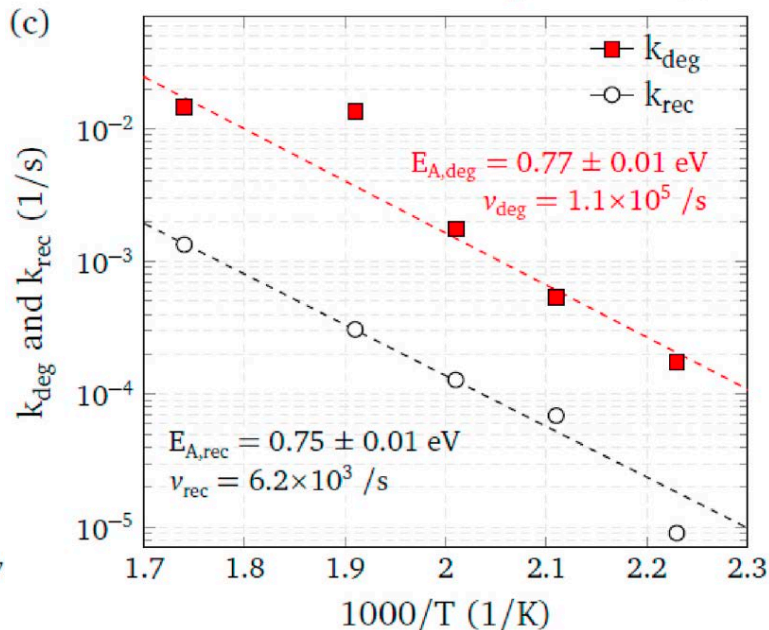


# Poly-Si/SiO<sub>2</sub> Degradation/Regeneration Cycle have Similar E<sub>activation</sub>

T<sub>fire</sub> = 777 °C



$$k = \nu e^{\frac{-E_{act}}{RT}}$$



- Similar E<sub>act</sub> for degrade and regen modes
- ν differ by ~ 100 which may help distinguish nature of processes.

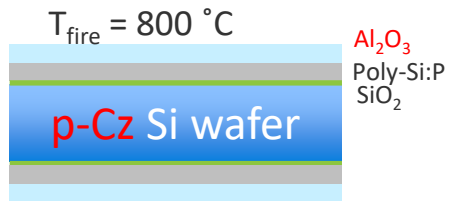
Chen et al., Solar Energy Materials & Solar Cells 236 (2022) 111491



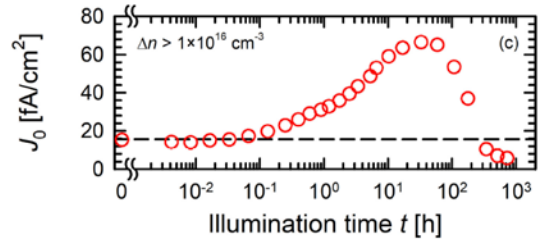
“TOPCon Solar Cell Degradation via Pinhole Nucleation”,  
Molecular Dynamics Simulations, Gergely T. Zimanyi, UC Davis, PVSC 2023



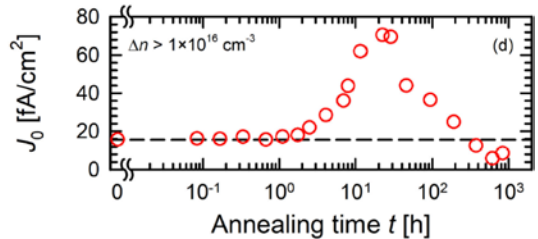
# Poly-Si/SiO<sub>2</sub> Degradation/Regeneration Cycle with Fired Al<sub>2</sub>O<sub>3</sub>



Light anneal: 1-Sun, 185 °C

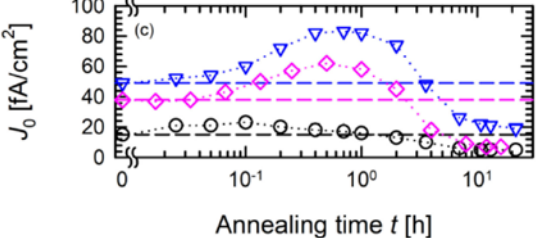


Dark anneal: 200 °C

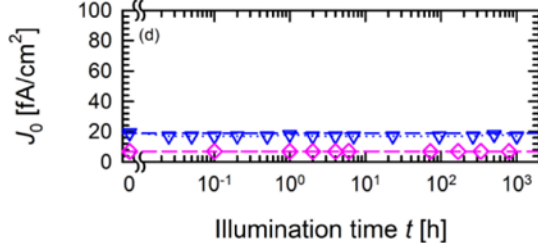


- Fired Al<sub>2</sub>O<sub>3</sub> is similar to fired SiN<sub>x</sub>
- After degrade/regen cycle  $J_0$  improves beyond the as-deposited state
- Dark anneal gives same result at light anneal

Dark anneal: 300 °C

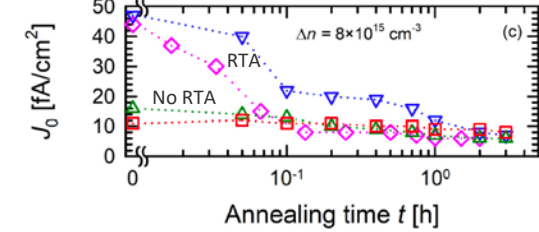


1-Sun, 80 °C

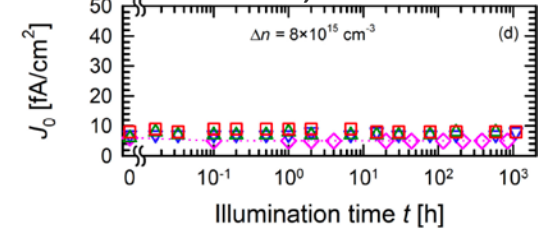


- Dark anneal at 300 °C gives similar results but 100 x faster compared with 200 °C anneal
- 1-sun, 80 °C anneal shows poly-Si/SiO<sub>2</sub> contact is stable to 1000 hrs

Dark anneal: 400 °C



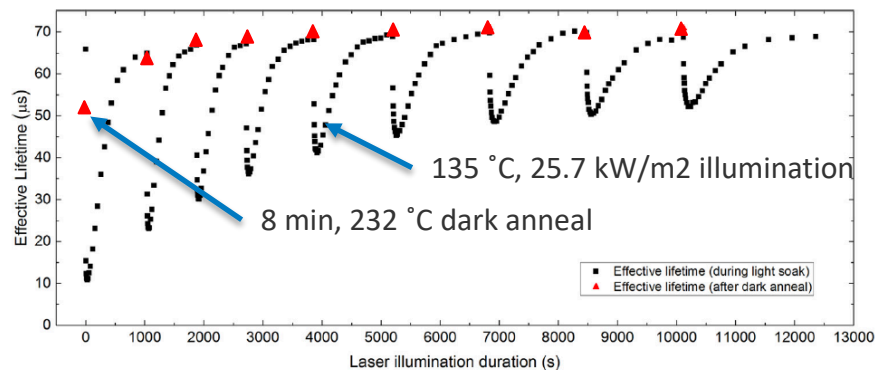
1-Sun, 80 °C



- Dark anneal at 400 °C improves  $J_0$  10 x faster than 300 °C anneal
- No degradation seen, only regen in  $J_0$
- $J_0 < 10\text{ fA/cm}^2$  after 6 mins for “typical” TOPcon processing steps.
- $J_0$  remains stable to 1000 hrs with 1-Sun, 80 °C anneal

# Poly-Si/SiO<sub>2</sub> long-term stability

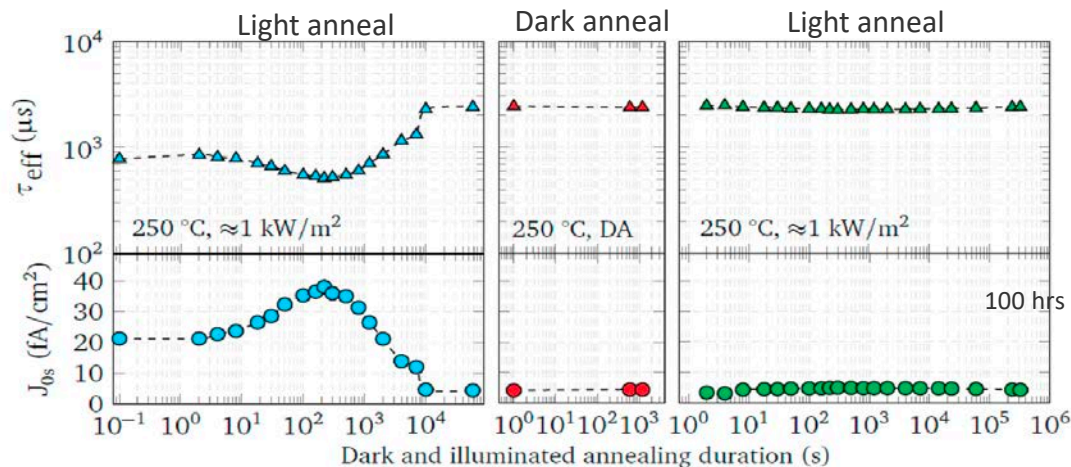
LeTID



- LeTID can be “reset” after a dark anneal.

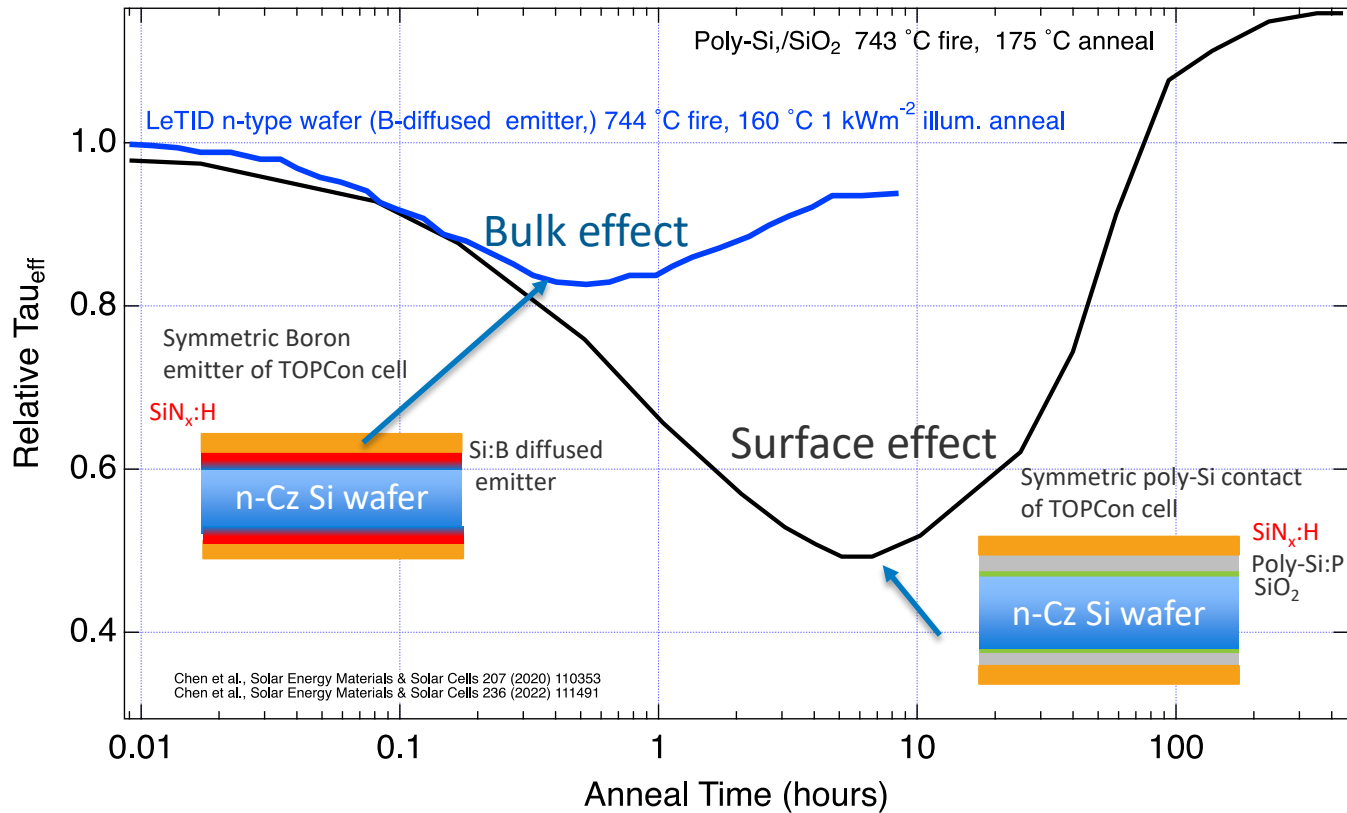
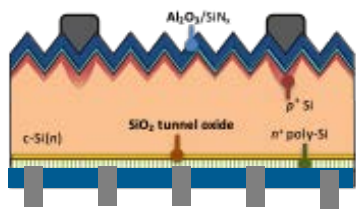
Fung et al., Solar Energy Materials and Solar Cells 184 (2018) 48–56

Poly-Si/SiO<sub>2</sub> contact



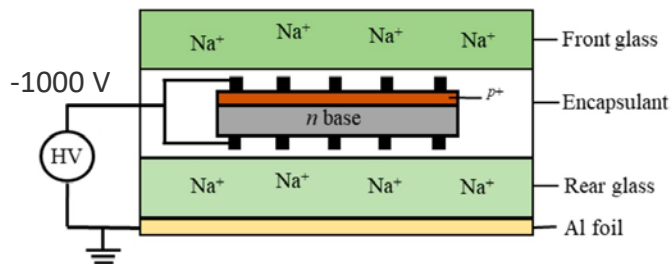
- Poly-Si/SiO<sub>2</sub> passivation remains stable after initial degrade/regen cycle

# Compare LeTID with Poly-Si/SiO<sub>2</sub> degradation

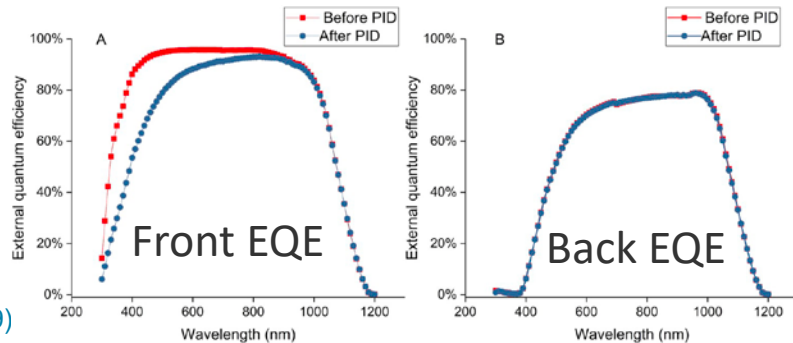


- LeTID in n-type materials is small and fast compared with TOPCon contact surface degradation
- TOPCon contact degrade/regen cycle < 100 hrs at 175 °C
- TOPCon improves beyond as-fired state.

# TOPCon Module Studies: PID

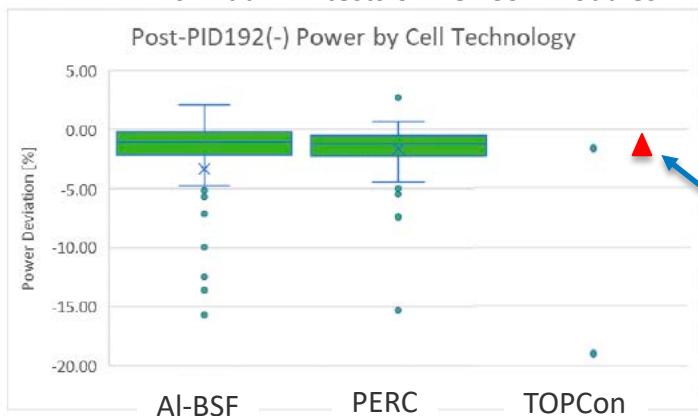


Lou et al., Solar Energy Materials and Solar Cells 195 (2019)



- Polarization PID seen in B-emitter
- Poly-Si contact showed no degradation.

## PVEL's initial PID tests on TOPCon modules



- Only two TOPCon modules tested
- one passed PID test <2% degradation
- one failed ~18% degradation

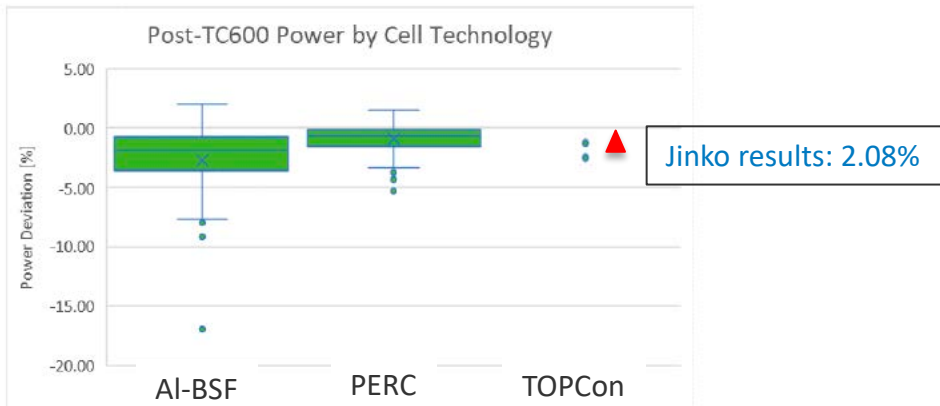
Jinko results: 1.03%

PVEL report "Demonstration durability in n-type modules",  
Tristan Erion-Lorico, PV Mag. Webinar Aug. 30, 2022

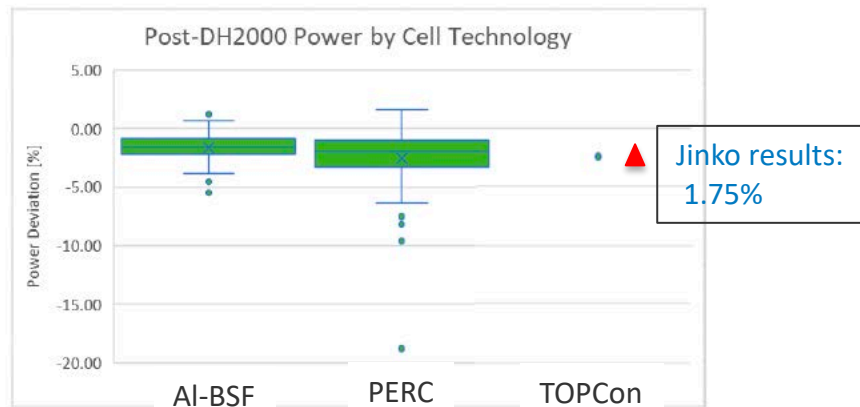
"The Role of PV Technologies in Enhancing PV Module Reliability"  
Mohammed Saady Dweik, Jinko Solar  
PV Mag. Webinar Aug. 30, 2022

# PVEL TOPcon Report, Jinko Tests

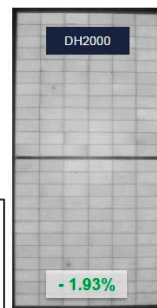
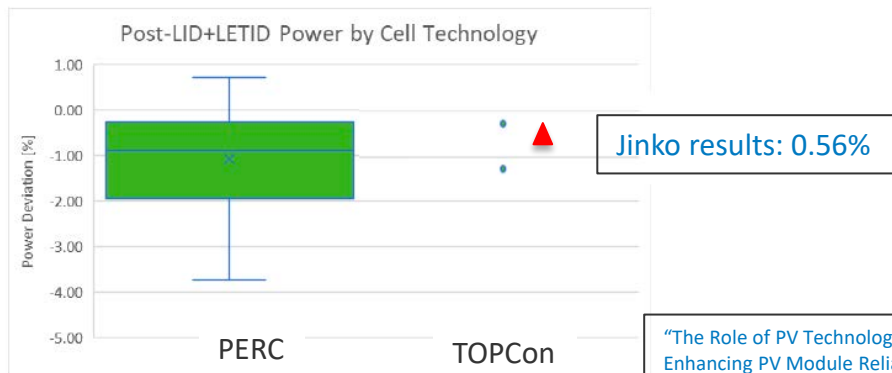
## Thermal Cycling



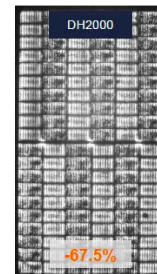
## Damp heat



## LID + LeTID



- › N-type TOPCon
- › Strong damp heat results



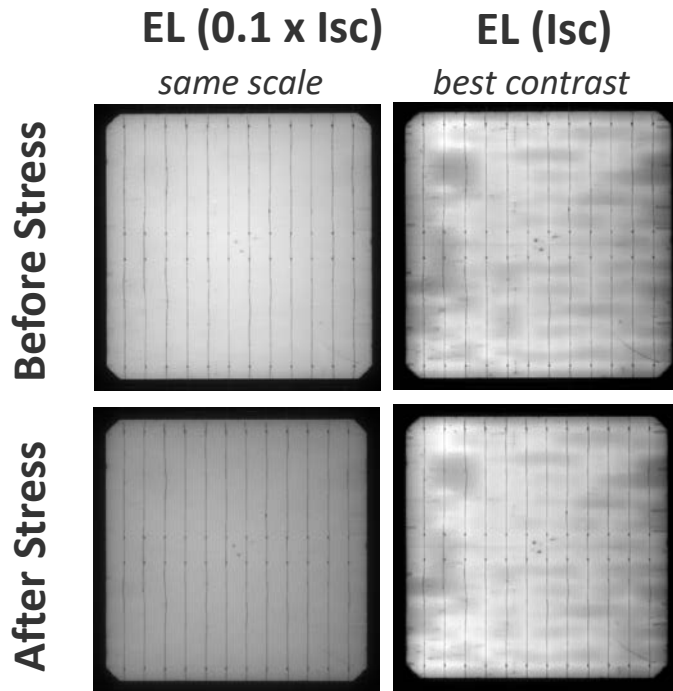
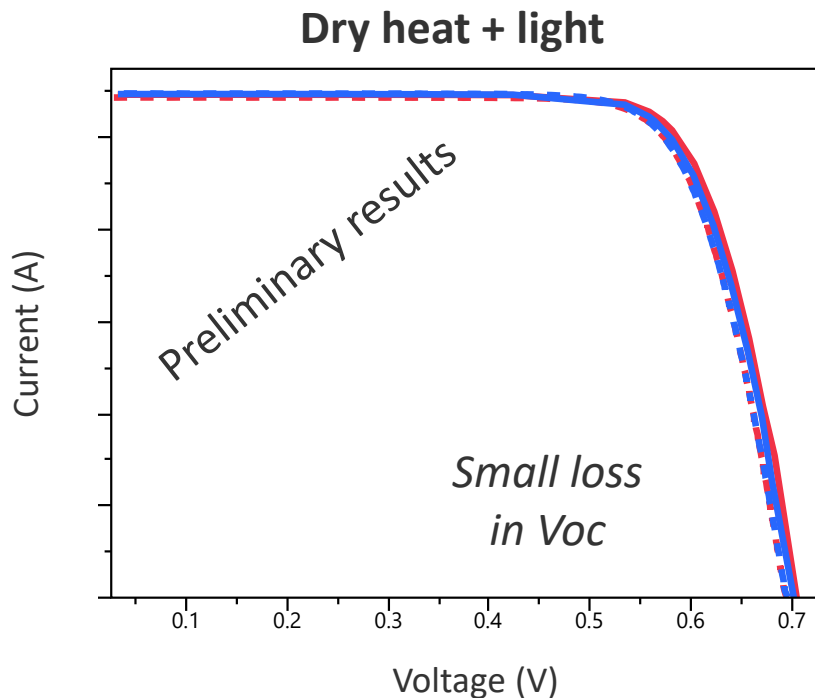
- › N-type TOPCon
- › Worst damp heat results in PVEL history



# Prototype TOPCon modules Accelerated Screen Testing

Stay tuned

NREL, ASU and a top-tier module manufacturer are studying TOPCon mini-modules



# Early TOPCon Modules Tests

- Jolywood: LID test +0.5% power gain, LeTID test +1% power gain.
- Jolywood and Jinko TOPCon modules are guaranteed < 1% degradation in the first-year, < 0.4% annual degradation
- [PVEL Top Performer Score Card](#):  
ET Solar Inc. has one TOPCon module that was scored a top performer in LID + LeTID and Thermal Cycling

# Conclusions: Degradation Mechanisms in TOPCon/POLO Solar Cells

- Poly-Si/SiO<sub>2</sub> contacts show a post firing degradation/regeneration cycle
- Cycle changes surface passivation ( $J_0$ ), but not the bulk lifetime
- Cycle time depends on anneal temperature in light or dark. (higher T, faster cycle)
- 400 °C anneal eliminates the cycle -> only generation occurs
- Cycle time and magnitude is not correlated with  $T_{\text{fire}}$
- Contact passivation is stable after cycling
- Fundamental nature of defect(s) responsible is not known
- TOPCon cells/modules, if constructed well, seem to show minimal degradation issues (PVEL, Jolywood, Jinko, ET Solar)
- NREL/ASU are studying TOPCon cells and UC Davis has a molecular dynamics model for TOPCon – *stay tuned*

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# Thank You

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